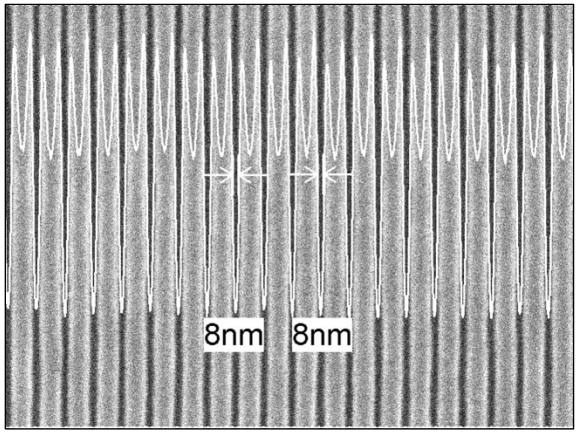
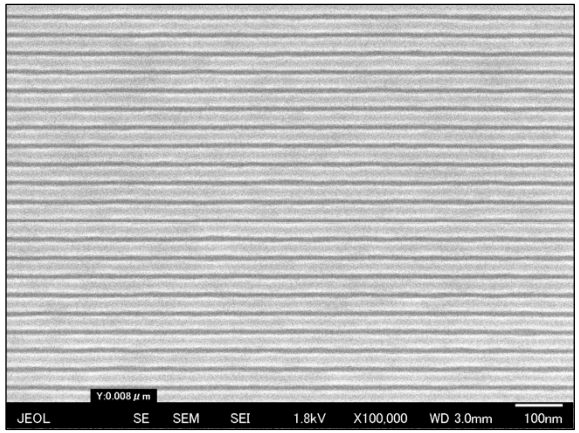
Site Acceptance Test Results

JEOL JBX-6300FS Direct Write E-Beam Lithography System

	ITEMS			Conditions	Measurements	Specification	Results	
1	Minimum line width	Measurement at field center		Acc. Volt: 100kV	At field center	8nm or less	X	Y
							8.0 nm	8.0 nm
2	Mask writing performance	1)	Field stitching accuracy	Acc. Volt: 100kV	Pattern position measurement (LEICA IPRO)	+/- 20nm or less	Min	Max
							-8.5 nm	8.3 nm
3	Direct writing performance	1)	EB-EB overlay accuracy	Acc. Volt: 100kV	Pattern position measurement (LEICA IPRO)	+/- 20nm or less	Min	Max
							-2.2 nm	9.2 nm
		2)	Field stitching accuracy			+/- 20nm or less	Min	Max
							-6.2 nm	9.2 nm





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